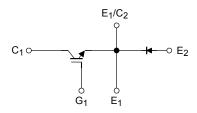
TOSHIBA GTR Module Silicon N Channel IGBT

MG150J1JS50

High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- High input impedance
- Includes a complete half bridge in one package.
- Enhancement-mode
- High speed : t_f = 0.30 μs (max) (IC = 150 A) t_{rr} = 0.15 μs (max) (IF = 150 A)
- ullet Low saturation voltage
 - $: V_{CE (sat)} = 2.70 \text{ V (max) (IC} = 150 \text{ A)}$

Equivalent Circuit



Unit: mm 2-\$5.4±0.3 3-M5 2-FAST-ON-TAB #110 JAPAN JAPAN 2-\$5.4±0.5 3-M5 2-FAST-ON-TAB #110 3-M5 3-M5 3-M5 2-FAST-ON-TAB #110 3-M5 3-M5

Maximum Ratings (Ta = 25°C)

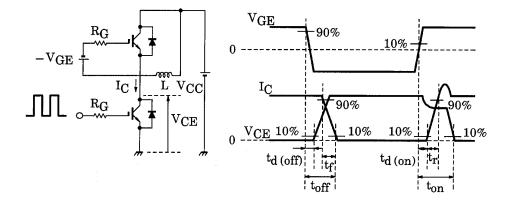
| Characteristics | | Symbol | Rating | Unit | |
|---|------|-------------------|---------------------|------|--|
| Collector-emitter voltage | | V _{CES} | 600 | V | |
| Gate-emitter voltage | | V _{GES} | ±20 | V | |
| Reverse voltage | | V _R | 600 | V | |
| Collector current | DC | I _C | 150 | A | |
| | 1 ms | I _{CP} | 300 | | |
| Forward current | DC | I _F | 150 | А | |
| | 1 ms | I _{FM} | 300 | | |
| Collector power dissipation (Tc = 25°C) | | PC | 780 | W | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | -40 to 125 | °C | |
| Isolation voltage | | V _{Isol} | 2500 (AC 1 min.) | V | |
| Screw torque (Terminal/mounting) | | _ | 3/3 | N·m | |

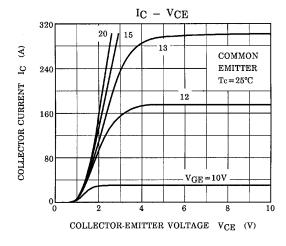


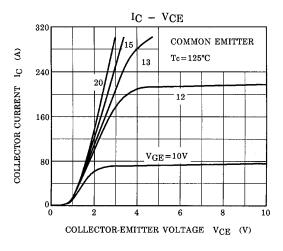
Electrical Characteristics (Ta = 25°C)

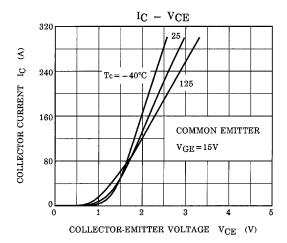
| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|---------------------|-----------------------|--|----------|-------|------|------|
| Gate leakage current | | I _{GES} | V _{GE} = ±20 V, V _{CE} = 0 | _ | _ | ±500 | nA |
| Collector cut-off current | | I _{CES} | V _{CE} = 600 V, V _{GE} = 0 | _ | _ | 2.0 | mA |
| Gate-emitter cut-off voltage | | V _{GE (off)} | I _C = 15 mA, V _{CE} = 5 V | 5.0 | 7.0 | 8.0 | V |
| Collector-emitter saturation voltage | | V _{CE (sat)} | I _C = 150 A,V _{GE} = 15 V | _ | 2.10 | 2.70 | ٧ |
| Input capacitance | | C _{ies} | V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz | _ | 14200 | _ | pF |
| Switching time | Turn-on delay time | t _{d (on)} | Inductive load $V_{CC}=300 \text{ V}$ $I_{C}=150 \text{ A}$ $V_{GE}=\pm15 \text{ V}$ $R_{G}=6.2 \Omega$ (Note 1) | _ | 0.15 | 0.30 | μs |
| | Rise time | t _r | | _ | 0.15 | 0.30 | |
| | Turn-on time | t _{on} | | _ | 0.50 | 1.00 | |
| | Turn-off delay time | t _{d (off)} | | _ | 0.20 | 0.40 | |
| | Fall time | t _f | | _ | 0.15 | 0.30 | |
| | Turn-off time | t _{off} | | _ | 0.50 | 1.00 | |
| Reverse current | | I _R | V _R = 600 V | _ | _ | 1.0 | mA |
| Forward voltage | | V _F | I _F = 150 A, V _{GE} = 0 | _ | 2.30 | 3.00 | V |
| Reverse recovery time | | t _{rr} | $I_F = 150 \text{ A}, V_{GE} = -10 \text{ V}$ di/dt = 200 A/ μ s | _ | 0.08 | 0.15 | μs |
| Thermal resistance | | R _{th (j-c)} | Transistor stage | — — 0.16 | | 0.16 | °C/W |
| | | | Diode stage | _ | _ | 0.35 | C/VV |

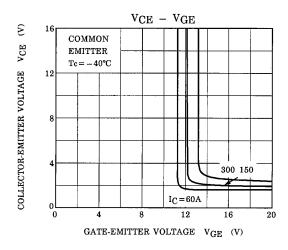
Note 1: Switching time test circuit & timing chart

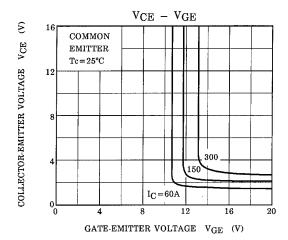


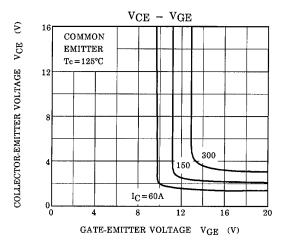


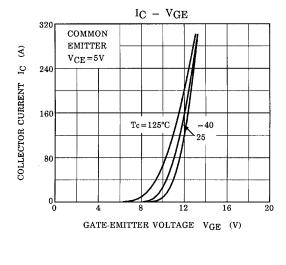


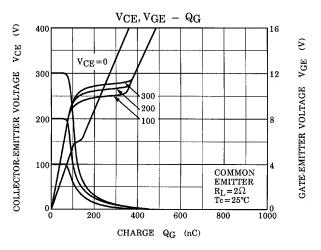


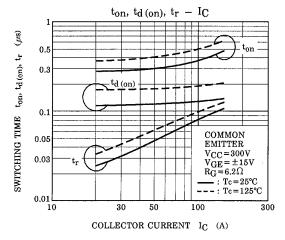


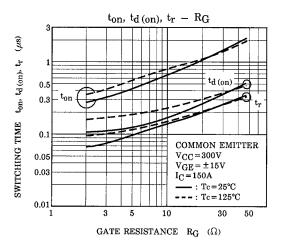


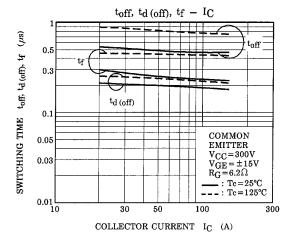


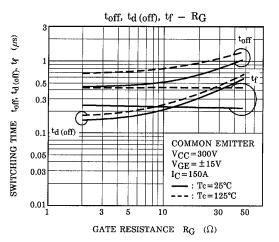


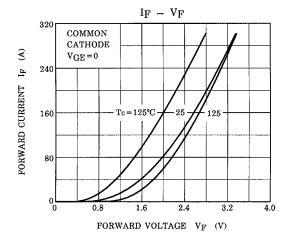


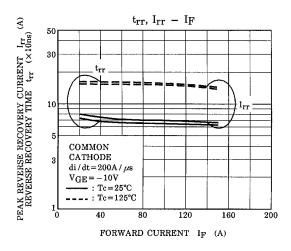


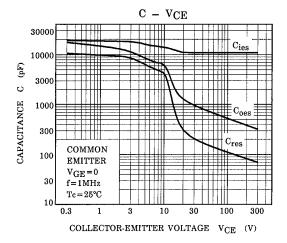


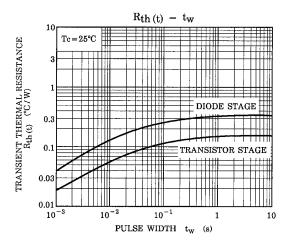


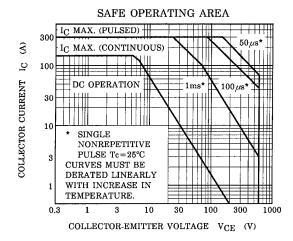


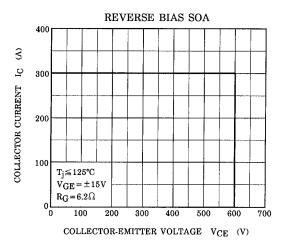












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